PATENT ABSTRACTS OF JAPAN

(11) Publication number:

2001119040 A

(43) Date of publication of application: 27.04.01

(51) Int. CI

H01L 29/84 G01P 15/125

(21) Application number: 11295500

(22) Date of filing: 18.10.99

(71) Applicant:

DENSO CORP

(72) Inventor:

YAMAMOTO TOSHIMASA **TAKEUCHI YUKIHIRO**

KATO NOBUYUKI

(54) SEMICONDUCTOR AMOUNT-OF-DYNAMICS SENSOR AND MANUFACTURING METHOD **THEREFOR**

(57) Abstract:

PROBLEM TO BE SOLVED: To provide semiconductor amount-of-dynamics sensor readily securing a closing property in a cap when protecting the movable part of beam structure with the cap.

SOLUTION: A sensor element part, consisting of a beam structure 2 as a movable part, fixed electrodes 9a-9c, and the like, is provided on the upper surface of a silicon substrate 17, an insulated and separated conductive thin film 19 is embedded between a sensor element part and the substrate 17, a wiring pattern and lower electrodes 22-25 formed by the conductive thin film 19 are electrically connected to electrode take-out parts 27a-27d arranged being nearly flush with the sensor element part, at the same time, a flat part 30 without steps so that the sensor element part is surrounded is formed between the electrode draw-out part on the substrate 17 and the sensor element, one surface side of a cap substrate 200

with a recessed part 202 at one surface side is joined to the flat part 30, and the sensor element part is covered with the recessed part 202 for protection.

COPYRIGHT: (C)2001,JPO

